

semiconductor 10 through the oxide 18 creates electron-hole pairs. The negatively charged electrons are attracted to the surface of the semiconductor by the positive charge 20 and 22 in the oxide 18, while the positively charged holes are repelled into the bulk of the semiconductor. The electrons are minority carriers in p-type semiconductors. When they reach the interface between the semiconductor 10 and the oxide 18, they are measured by an apparatus to be described later. However, the number of electrons reaching the interface is determined by the minority lifetime or, alternatively, the recombination rate. Therefore in an area of the semiconductor 10, where a defect causes increased recombination or decreased minority lifetime, the number of electrons reaching the interface is reduced with a corresponding reduction in the signal. Thus a map of the detected signal of electrons at the surface will be an inverse map of the defect distribution affecting the minority lifetime in the semiconductor.

Detailed Description Text - DETX (9):

In use, both ends of the board 90 are mechanically fixed and the wafer 68 slowly passes beneath the electrode assembly. It has been found that a separation of 50 to 500 .mu.m between the electrodes 70 and 76 and the upper

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Sheet 1 of 2 4,599,558

FIG. 1

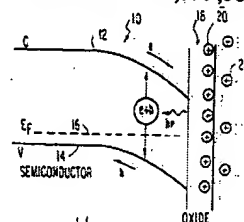
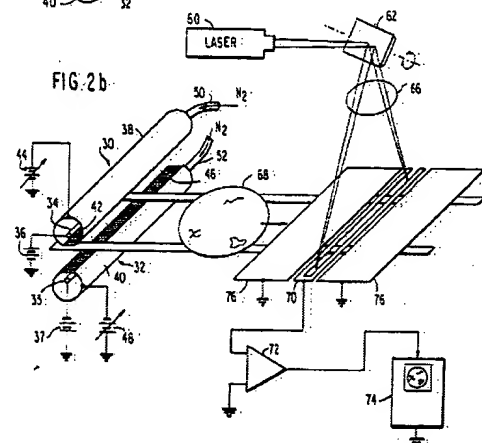


FIG. 2a



FIG. 2b



Details Text Image HTML KWIC

Document ID	Kind Codes	Source	Issue Date	Pages	
1 US 20020021141		US-PGPUB	20020221	5	App
2 US 6316950 B1		USPAT	20011113	6	Metl
3 US 5138256 A		USPAT	19920811	7	Metl
4 US 4827212 A		USPAT	19890502	12	Non
5 US 4599558 A		USPAT	19860708	8	Pho
6 US 4473795 A		USPAT	19840925	11	Sys
7 US 3995216 A		USPAT	19761130	13	Tec

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